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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 4

Complete if Known	
Application Number	10/776,572
Filing Date	02-11-2004
First Named Inventor	Jaiprakash et al.
Art Unit	2815
Examiner Name	TBA
Attorney Docket Number	112020.144US2 NAN-20

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Signature		Date Considered	2/2/2005

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Filing Date	02-11-2004
First Named Inventor	Jaiprakash et al.
Art Unit	2815
Examiner Name	TBA
Attorney Docket Number	112020.144US2 NAN-20

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				First Named Inventor	Jaiprakash et al.
				Art Unit	2815
				Examiner Name	TBA
Sheet	4	of	4	Attorney Docket Number	112020.144US2 NAN-20

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